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INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				Application Number	10/813,233
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				First Named Inventor	Shunpei YAMAZAKI et al.
				Art Unit	2823
				Examiner Name	Trung Q. Dang
Sheet	1	of	1	Attorney Docket Number	740756-2719

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Examiner Initials ¹	Cite No. ¹	U.S. Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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Examiner Signature	T. DANG	Date Considered	6/24/05
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